

<b>SANYO</b>	No.2458	<h2 style="margin: 0;">2SA1572/2SC4067</h2> <p style="margin: 0;">PNP/NPN Epitaxial Planar Silicon Transistors</p> <p style="margin: 0;">Switching Applications (with Bias Resistance)</p>
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**Applications**

- . Switching circuit, inverter circuit, interface circuit, driver circuit

**Features**

- . On-chip bias resistance: R1=0, R2=47kΩ
- . Small-sized package: SPA

( ): PNP

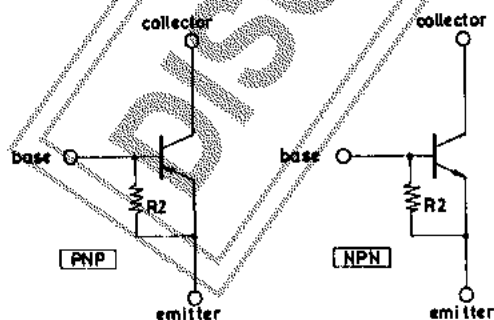
**Absolute Maximum Ratings at Ta=25°C**

			unit
Collector to Base Voltage	$V_{CB0}$	(-)50	V
Collector to Emitter Voltage	$V_{CEO}$	(-)50	V
Emitter to Base Voltage	$V_{EBO}$	(-)5	V
Collector Current	$I_C$	(-)100	mA
Collector Current(Pulse)	$I_{CP}$	(-)200	mA
Collector Dissipation	$P_C$	300	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C

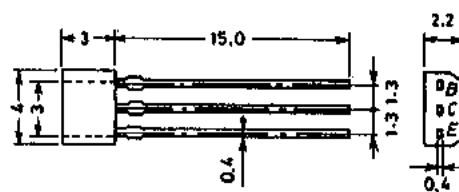
**Electrical Characteristics at Ta=25°C**

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=(-)40V, I_E=0$			(-)0.1	μA
	$I_{CEO}$	$V_{CE}=(-)40V, I_B=0$			(-)0.5	μA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=(-)5V, I_C=0$	(-)81	(-)106	(-)151	μA
DC Current Gain	$h_{FE}$	$V_{CE}=(-)5V, I_C=(-)10mA$	80			
Gain-Bandwidth Product	$f_T$	$V_{CE}=(-)10V, I_C=(-)5mA$		250		MHz
				(200)		
Output Capacitance	$c_{ob}$	$V_{CB}=(-)10V, f=1MHz$		3.7		pF
				(5.5)		
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)10mA, I_B=(-)0.5mA$			(-)0.1(-)0.3	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-)50			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)100\mu A, R_{BE}=\infty$	(-)50			V
Resistance	R2		33	47	61	kΩ

**Electrical Connection**



**Case Outline 2033 (unit:mm)**



B: Base  
C: Collector  
E: Emitter  
SANYO: SPA

Specifications and information herein are subject to change without notice.

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